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**Corrigendum: “Reliability of piezoelectric films for MEMS” [Jpn. J. Appl. Phys. **62**, SM0802 (2023)]**Susan Trolrier-McKinstry<sup>1\*</sup>, Wanlin Zhu<sup>1</sup>, Betül Akkopru-Akgun<sup>1</sup>, Fan He<sup>1</sup>, Song Won Ko<sup>2</sup>, Charalampos Fragkiadakis<sup>3</sup>, and Peter Mardilovich<sup>3</sup><sup>1</sup>*Pennsylvania State University, United States of America*<sup>2</sup>*Qi2, United States of America*<sup>3</sup>*aixACCT Systems GmbH, Germany*\*E-mail: [stmckinstry@psu.edu](mailto:stmckinstry@psu.edu)

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The numerical values in the last column in Table I should be corrected as follows. The reason for the correction is an authors' error in writing. For additional clarity, the range of  $E_B$  values measured are included.

**Table I.** Comparison of gradient and gradient free PZT films.  $\epsilon_r$  is relative permittivity,  $P_r$  is remanent polarization,  $E_C$  is coercive field,  $E_i$  is imprint and  $E_B$  is electrical breakdown field. The imprint was measured after poling either field up or field down at 200 kV cm<sup>-1</sup> for 30 min at 150 °C. The polarization measurements were performed by driving the bottom electrode and the observed positive shift of the polarization loop indicated an initial field down imprint in both films, albeit more pronounced in the gradient free case.

	$\epsilon_r$	Tan $\delta$	$P_{r-}, P_{r+}$ ( $\mu\text{C cm}^{-2}$ )	$E_{c-}, E_{c+}$ (kV cm <sup>-1</sup> )	$E_i$ initial and after poling field down/up (kV cm <sup>-1</sup> )	$E_B$ field down/up (kV cm <sup>-1</sup> )
Gradient	1280	0.033	-15.3, 14.1	-20.3, 27.0	3.33, 9.43/-7.73	785 ± 16/818 ± 10
Gradient free	1470	0.035	-15.5, 9.0	-10.5, 28.5	8.9, 13.2/-3.25	793 ± 3/830 ± 15

This correction does not affect any other part of the article.